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(54) Title (EN): MICROELECTRONIC DEVICES DESIGNED WITH MOLD PATTERNING TO CREATE PACKAGE-LEVEL COMPONENTS FOR HIGH FREQUENCY COMMUNICATION SYSTEMS

(54) Title (FR): DISPOSITIFS MICROÉLECTRONIQUES CONÇUS AVEC UNE FORMATION DE MOTIFS DE MOULE POUR CRÉER DES COMPOSANTS AU NIVEAU DU BOÎTIER POUR DES SYSTÈMES DE COMMUNICATION HAUTE FRÉQUENCE

(57) Abstract:

(EN): Embodiments of the invention include a microelectronic device that includes a first substrate having radio frequency (RF) components and a second substrate that is coupled to the first substrate. The second substrate includes a first conductive layer of an antenna unit for transmitting and receiving communications at a frequency of approximately 4 GHz or higher. A mold material is disposed on the first and second substrates. The mold material includes a first region that is positioned between the first conductive layer and a second conductive layer of the antenna unit with the mold material being a dielectric material to capacitively couple the first and second conductive layers of the antenna unit.

(FR): Des modes de réalisation de l'invention concernent un dispositif microélectronique qui comprend un premier substrat ayant des composants radiofréquence (RF) et un second substrat qui est couplé au premier substrat. Le second substrat comprend une première couche conductrice d'une unité antenne pour émettre et recevoir des communications à une fréquence d'environ 4 GHz ou plus. Un matériau de moule est disposé sur les premier et second substrats. Le matériau de moule comprend une première région qui est positionnée entre la première couche conductrice et une seconde couche conductrice de l'unité d'antenne, le matériau de moule étant un matériau diélectrique pour coupler de manière capacitive les première et seconde couches conductrices de l'unité d'antenne.

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Declaration of inventorship (Rules 4.17(iv) and 51bis.1(a)(iv)) for the purposes of the designation of the United States of America